华润微电子(重庆)有限公司

CRST113N20N,CRSS109N20N

SkyMOS3 N-MOSFET 200V, 8.8mΩ, 105A

Features

- Uses CRM(CQ) advanced SkyMOS3 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent Q_gx$R_{DS(on)}$ product(FOM)
- Qualified according to JEDEC criteria

Product Summary

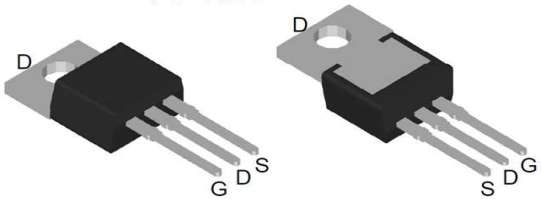
V_{DS}	200V
$R_{DS(on)}$	8.8mΩ
I_D	105A

Applications

- Motor control and drive
- Battery management
- UPS (Uninterrupible Power Supplies)

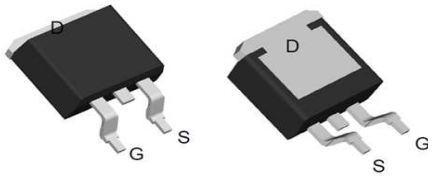
100% Avalanche Tested
100% DVDS Tested

TO-220

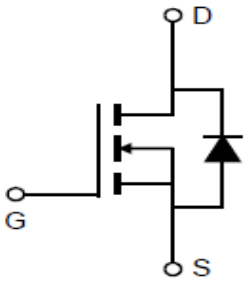


CRST113N20N

TO-263



CRSS109N20N



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRST113N20N	CRST113N20N	TO-220	Tube	N/A	N/A	50pcs
CRSS109N20N	CRSS109N20N	TO-263	Tube	N/A	N/A	50pcs

Absolute Maximum Ratings

Parameter	**Symbol**	**Value**	**Unit**
Drain-source voltage	V_{DS}	200	V
Continuous drain current T_C = 25°C (Silicon limit) T_C = 25°C (Package limit) T_C = 100°C (Silicon limit)	I_D	 105 160 67	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	420	A
Avalanche energy, single pulse (L=0.5mH, Rg=25Ω)[1]	$E_{AS(Note\ 1)}$	306	mJ
Gate-Source voltage	V_{GS}	±20	V
Power dissipation (T_C = 25°C)	P_{tot}	278	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

※. Notes:1.EAS is tested at starting Tj = 25℃, L = 0.5mH, IAS = 35A, Vgs=10V.

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Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.45	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	62.5	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Static Characteristic						
Drain-source breakdown voltage	BV_{DSS}	200	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	- -	- -	1 100	μA	V_{DS}=200V,V_{GS}=0V T_j=25°C T_j=125°C
Gate-source leakage current	I_{GSS}	-	-	100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	8.8 8.5	10.6 10.3	mΩ	V_{GS}=10V, I_D=50A TO-220 TO-263
Transconductance	g_{fs}	-	93	-	S	V_{DS}=5V,I_D=50A
Dynamic Characteristic						
Input Capacitance	C_{iss}	-	4819	-	pF	V_{GS}=0V, V_{DS}=100V, f=1MHz
Output Capacitance	C_{oss}	-	405	-		
Reverse Transfer Capacitance	C_{rss}	-	23	-		
Gate Total Charge	Q_G	-	69	-	nC	V_{GS}=10V, V_{DS}=100V, I_D=50A, f=1MHz
Gate-Source charge	Q_{gs}	-	25	-		
Gate-Drain charge	Q_{gd}	-	16	-		
Turn-on delay time	$t_{d(on)}$	-	16	-	ns	V_{DS}=100V I_D=50A R_G=2.7Ω V_{GS}=10V;
Rise time	t_r	-	82	-		
Turn-off delay time	$t_{d(off)}$	-	55	-		
Fall time	t_f	-	84	-		
Gate resistance	R_G	-	3.5	-	Ω	V_{GS}=0V, V_{DS}=0V, f=1MHz

Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.85	1.4	V	V_{GS}=0V,I_{SD}=50A
Body Diode Reverse Recovery Time	t_{rr}	-	129	-	ns	I_{SD}=50A, V_{GS}=0V, dIF/dt=100A/us;
Body Diode Reverse Recovery Charge	Q_{rr}	-	752	-	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

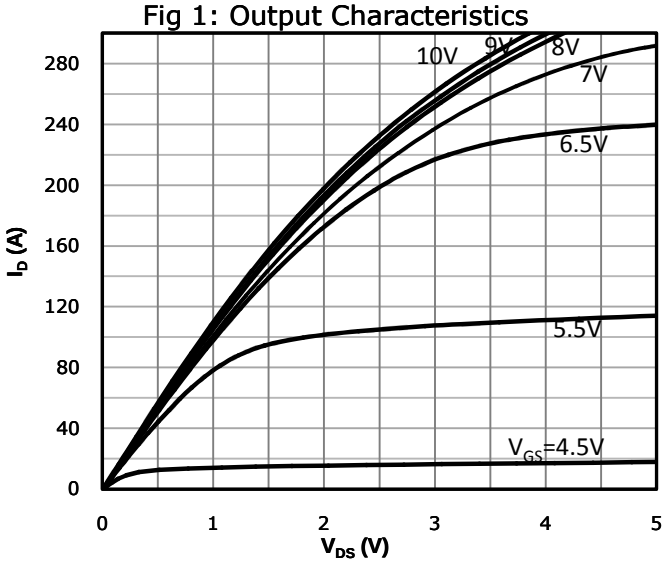


Fig 2: Transfer Characteristics

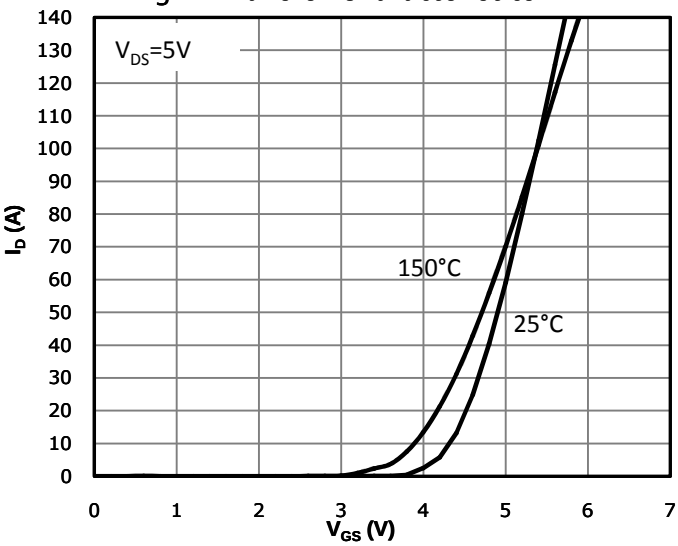


Fig 3: Rds(on) vs Drain Current and Gate Voltage

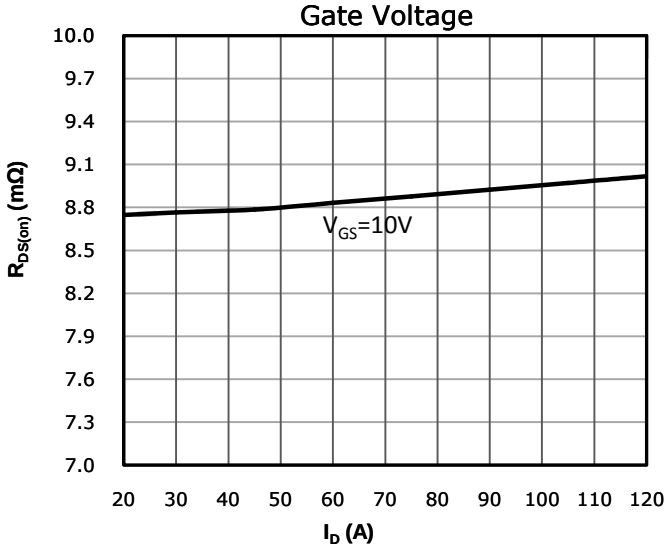


Fig 4: Rds(on) vs Gate Voltage

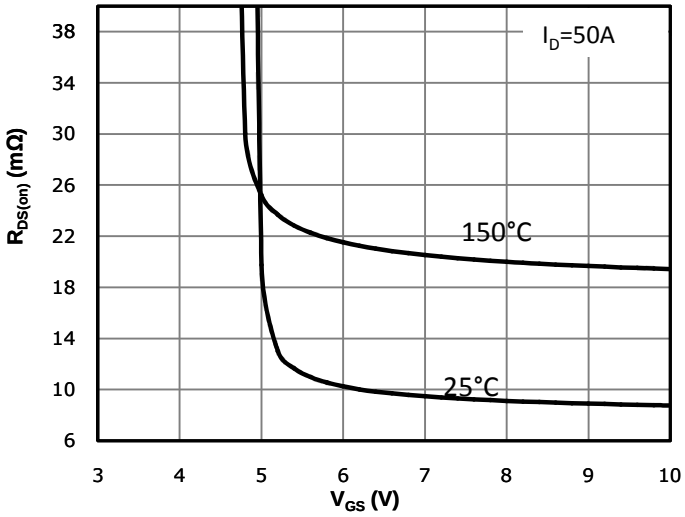


Fig 5: Rds(on) vs. Temperature

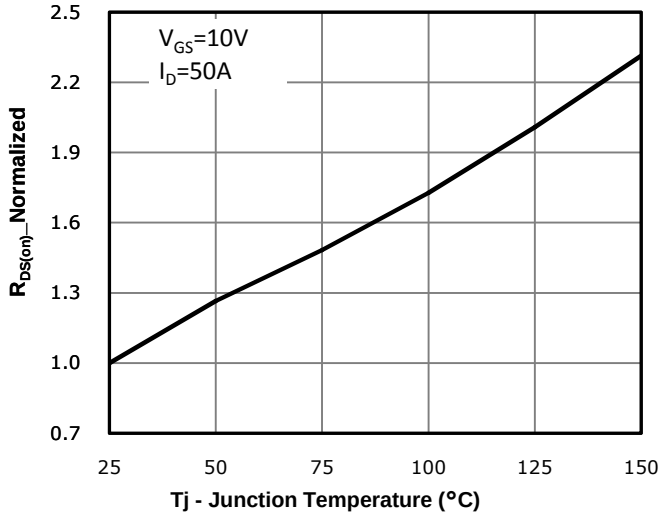
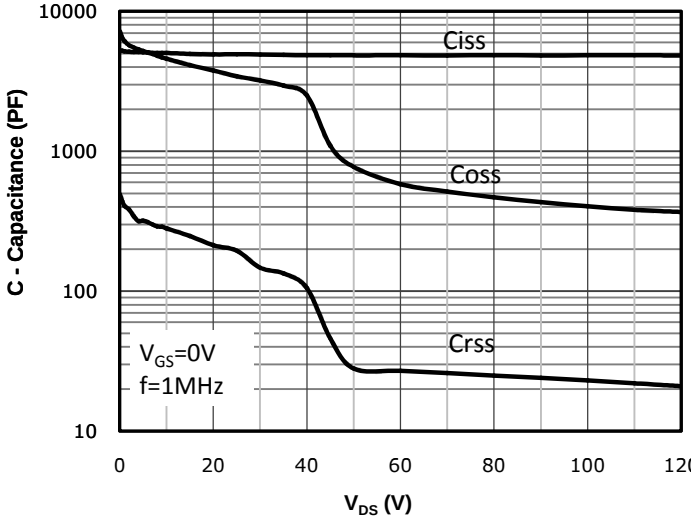


Fig 6: Capacitance Characteristics



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Fig 7: Gate Charge Characteristics

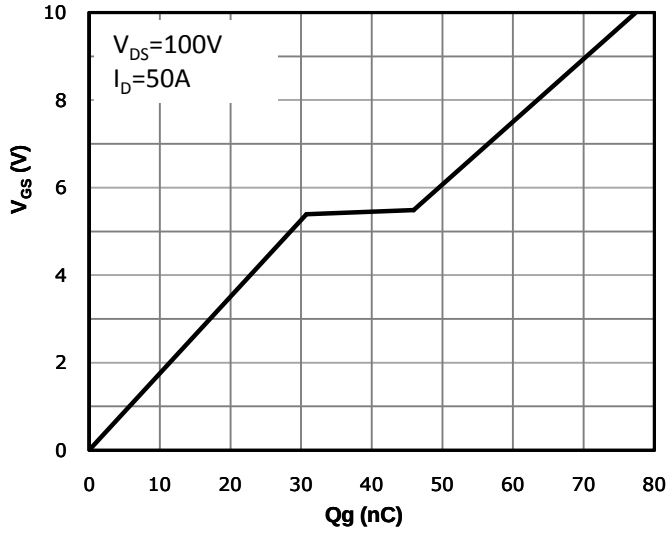


Fig 8: Body-diode Forward Characteristics

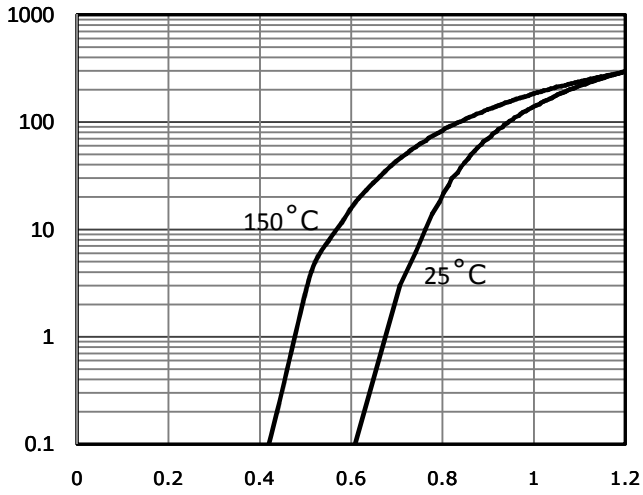


Fig 9: Power Dissipation

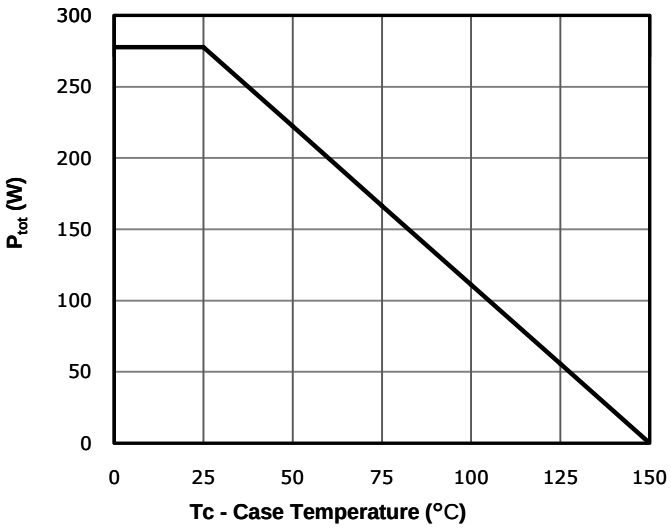


Fig 10: Drain Current Derating

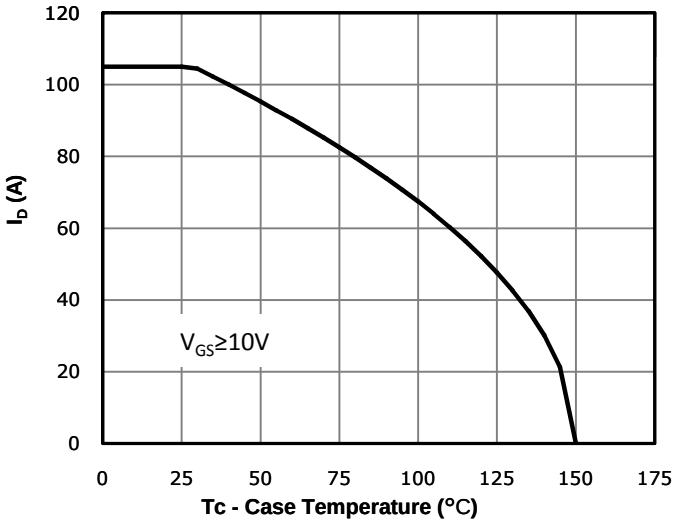


Fig 11: Safe Operating Area

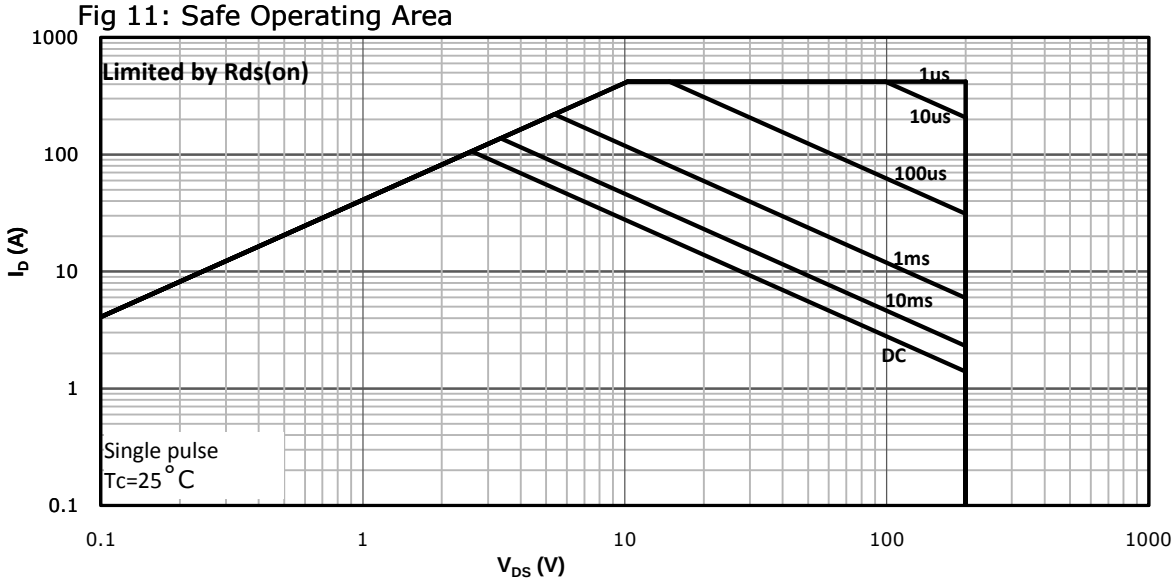
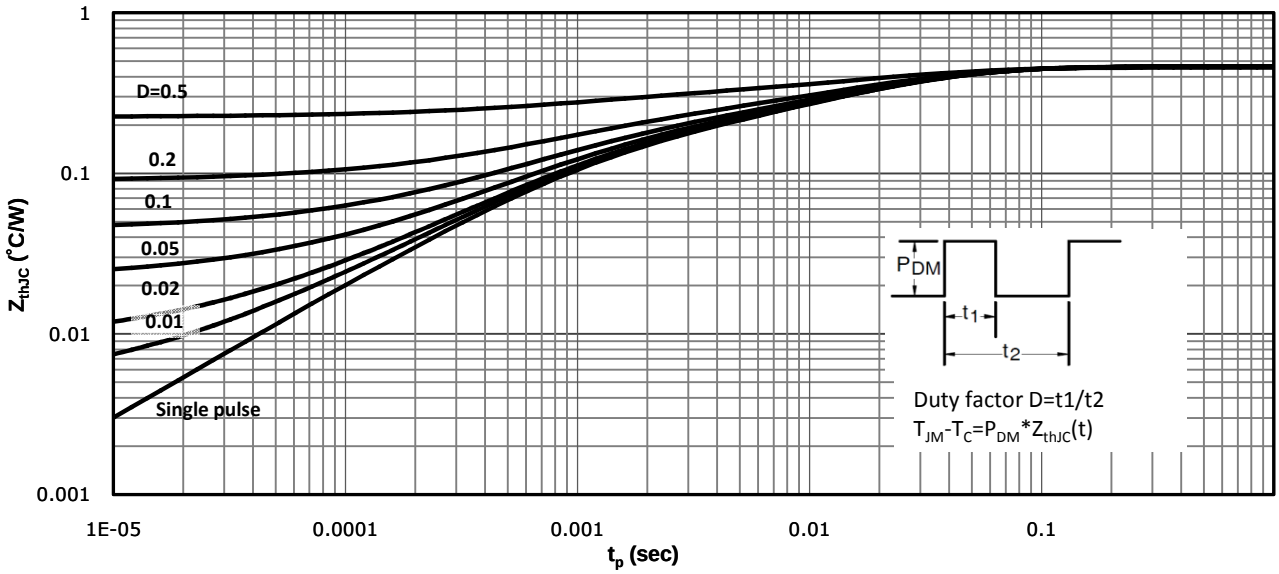
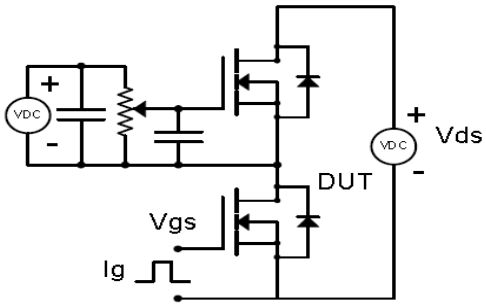


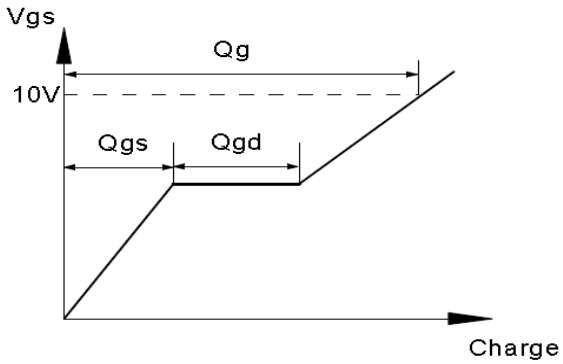
Fig 12: Max. Transient Thermal Impedance



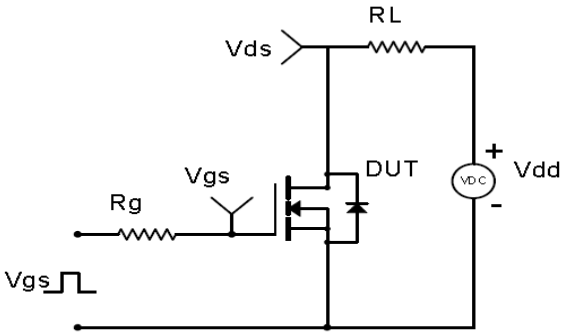
Test Circuit & Waveform

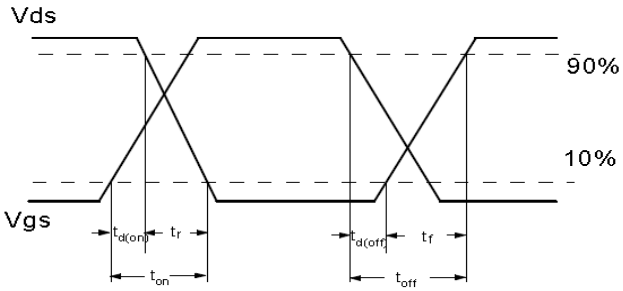
Gate Charge Test Circuit & Waveform



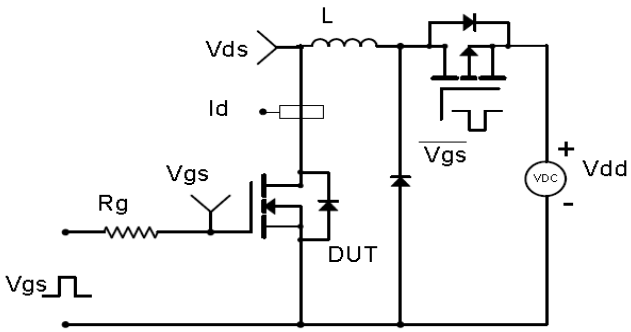


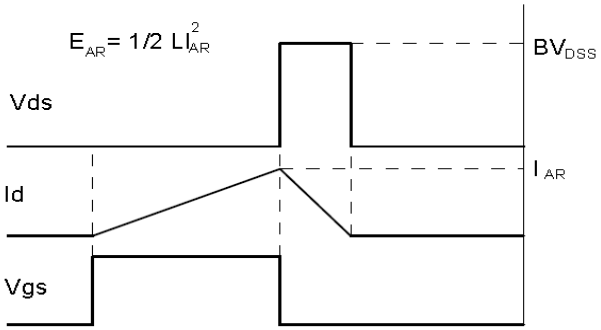
Resistive Switching Test Circuit & Waveforms



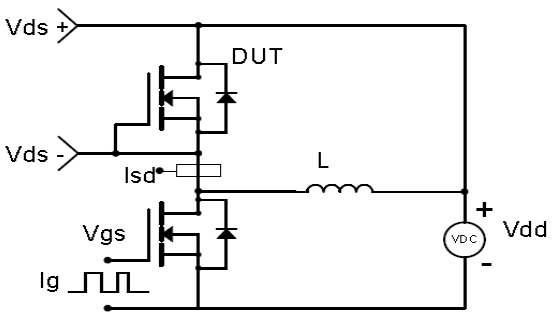


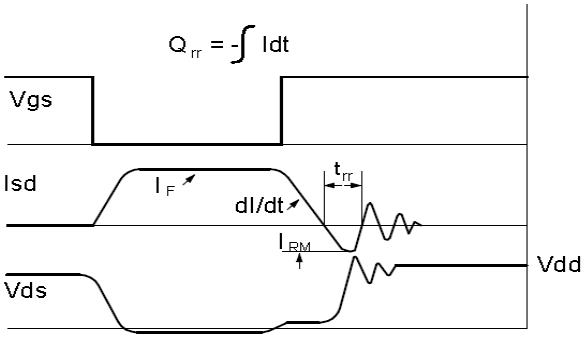
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



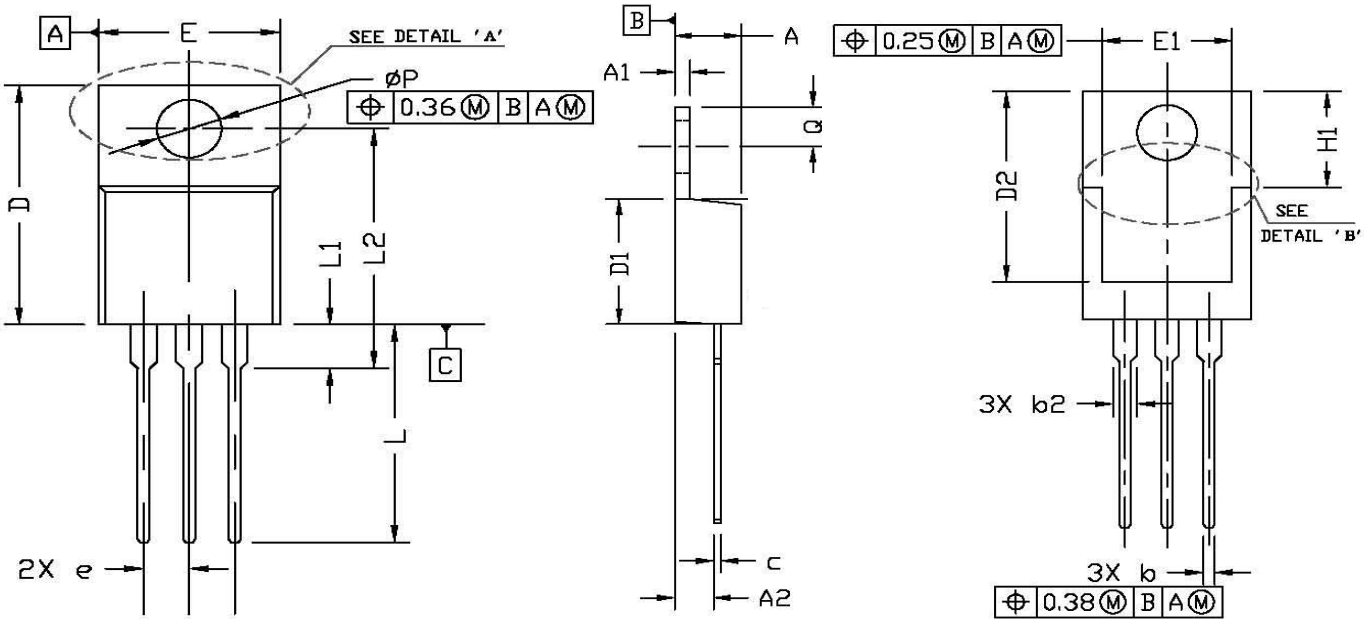


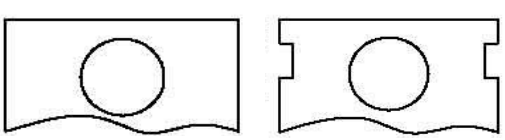
Diode Recovery Test Circuit & Waveforms





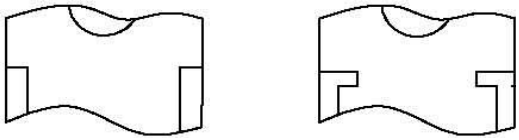
Package Outline: TO-220-3L





Option 1 Option 2

Detail 'A'



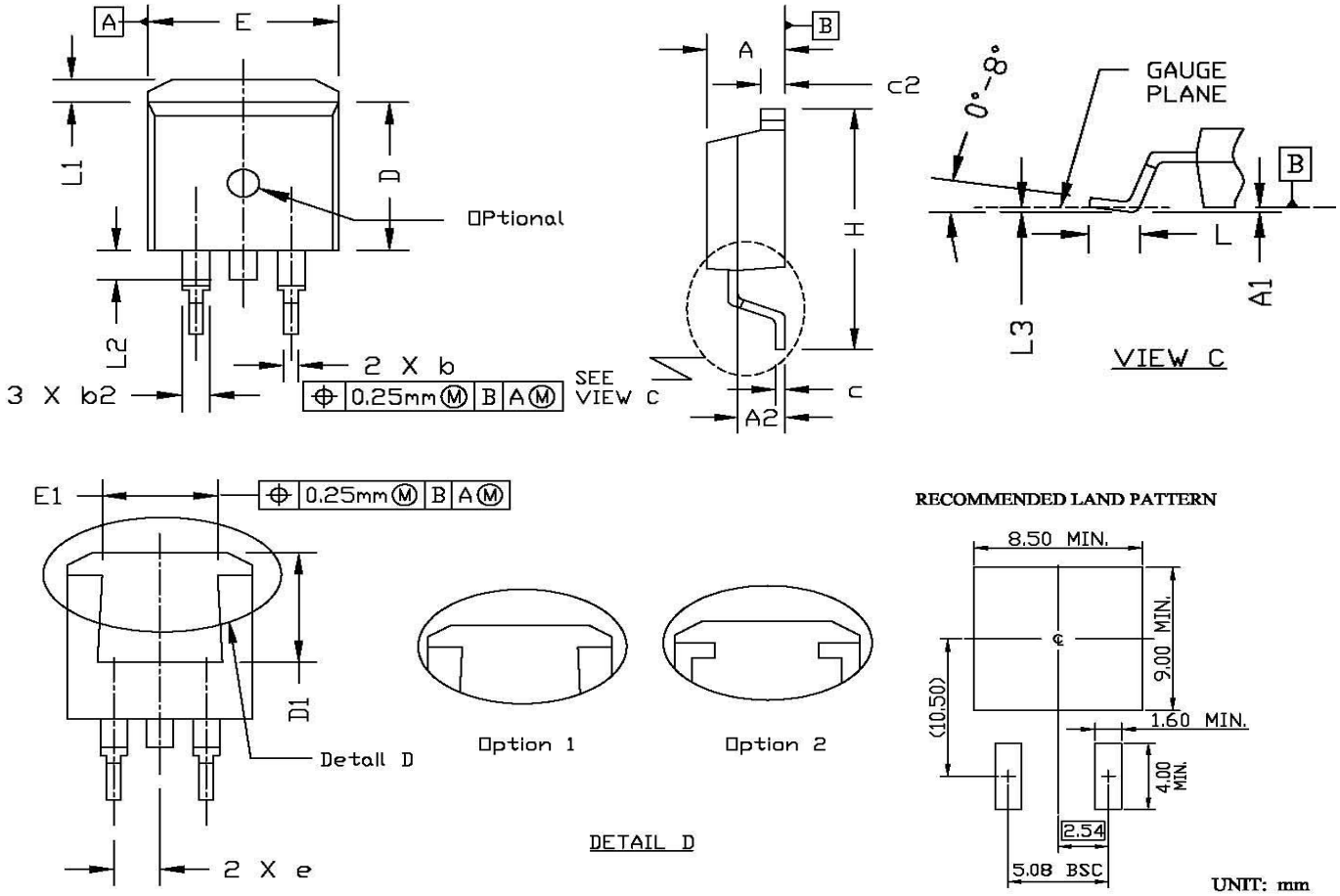
Option 1 Option 2

Detail 'B'

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.80	0.169	0.189
A1	1.20	1.45	0.047	0.057
A2	2.20	2.90	0.087	0.114
b	0.69	0.95	0.027	0.037
b2	1.00	1.60	0.039	0.063
c	0.33	0.65	0.013	0.026
D	14.70	16.20	0.579	0.638
D1	8.59	9.65	0.338	0.380
D2	11.75	13.60	0.463	0.535
e	2.54 BSC.		0.100 BSC.	
E	9.60	10.60	0.378	0.417
E1	7.00	8.46	0.276	0.333
H1	6.20	7.00	0.244	0.276
L	12.60	14.80	0.496	0.583
L1	2.70	3.80	0.106	0.150
L2	12.13	16.50	0.478	0.650
Q	2.40	3.10	0.094	0.122
P	3.50	3.90	0.138	0.154

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Package Outline: TO-263



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.30	4.86	0.169	0.191
A1	0.00	0.25	0.000	0.010
A2	2.34	2.79	0.092	0.110
b	0.68	0.94	0.027	0.037
b2	1.15	1.35	0.045	0.053
c	0.33	0.65	0.013	0.026
c2	1.17	1.40	0.046	0.055
D	8.38	9.45	0.330	0.372
D1	6.90	8.17	0.272	0.322
e	2.54 BSC.		0.100 BSC.	
E	9.78	10.50	0.385	0.413
E1	6.50	8.60	0.256	0.339
H	14.61	15.88	0.575	0.625
L	2.24	3.00	0.088	0.118
L1	0.70	1.60	0.028	0.063
L2	1.00	1.78	0.039	0.070
L3	0.00	0.25	0.000	0.010

Revision History

Revison	Date	Major changes
1.0	2019-05-14	Release of temporary version.
2.0	2019-09-29	Official version.

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.
Any and all semicondutor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
CRM(CQ) reserves the right to improve product design, function and reliability without notice.